

THIN FILM CAPACITIVE ELEMENT, METHOD FOR PRODUCING SAME
AND ELECTRONIC DEVICE

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ABSTRACT OF THE DISCLOSURE

10 An integrated thin film capacitive element
comprising a dielectric material of the specified
composition that exhibits increased voltage tunability of
capacitance and capacitance density and a production
process thereof are disclosed. The integrated thin film
15 capacitive element comprises a capacitor structure
constituted from a lower electrode, a dielectric layer
comprised of the high dielectric constant material
represented by the formula: $(\text{Ba}_{(1-y)(1-x)}\text{Sr}_{(1-y)x}\text{Y}_y)\text{Ti}_{1+z}\text{O}_{3+\delta}$ with
the range $0 < x < 1$, $0.007 < y < 0.02$, $-1 < \delta < 0.5$, and
20 $(\text{Ba}_{(1-y)(1-x)} + \text{Sr}_{(1-y)x})/\text{Ti}_{1+z} < 1$, and an upper electrode. An
electronic device comprising the capacitive element of
the present invention is also disclosed.